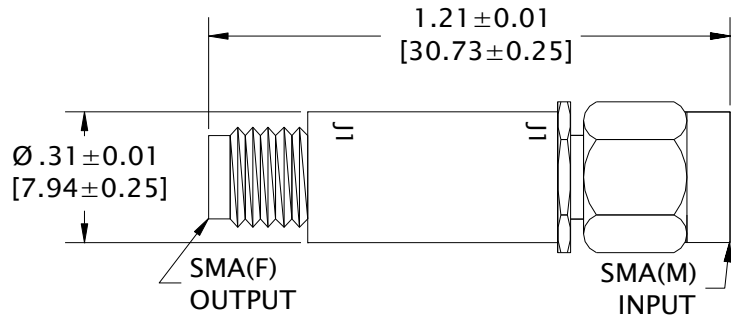


# Biased Schottky Diode Detector

2.0 to 18.0 GHz

**MODEL NO: ESS2018A3**

- Broadband Biased Detector
- Negative Output Polarity (-) is standard
- Max Input Power 200mW CW
- Operating Temperature: -55°C to +125°C
- Storage Temperature: -65°C to +150°C
- Specification @ 25°C, 100 µA Bias Typical, -20 dBm Input Power



Parameters	SPECIFICATION				Units
	FREQ. (GHz)	MIN	TYPICAL	MAX	
Voltage Sensitivity	2.0 to 18.0	1600	2500		mV/mW
Bias		80	100		µA
Tangential Sensitivity <sup>1</sup>	2.0 to 18.0		-55		dBm
Flatness	2.0 to 18.0			± 1.0	dB
Video Capacitance				20	pF
CW Power Handling				200	mWatt
Operating Temperature		-55		+125	°C

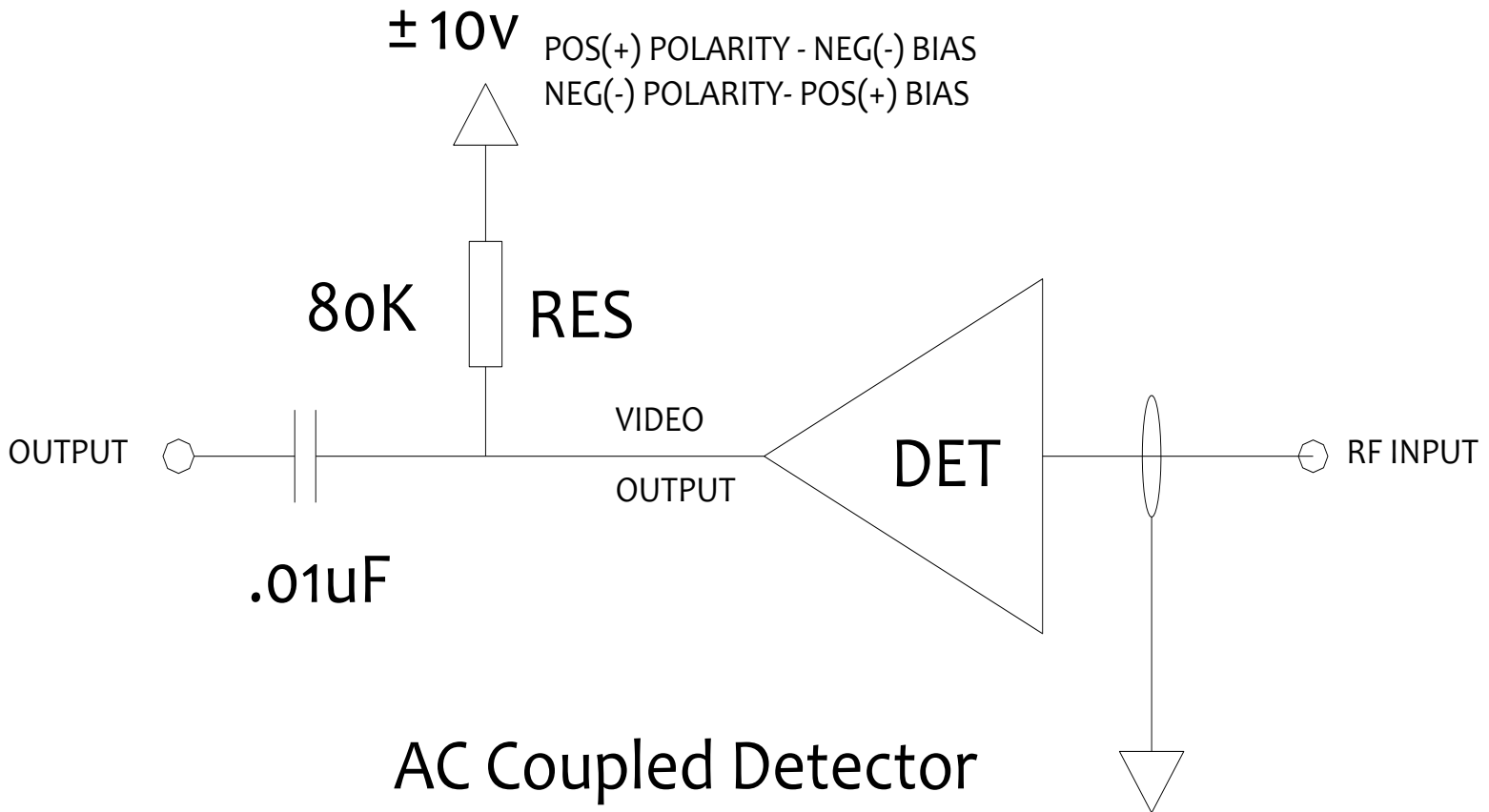
**NOTES:**

1. TSS is measured with a 2 MHz video bandwidth and 2 dB NF amplifier.
2. Typical values are measured at +25°C and are not guaranteed

# Biased Schottky Diode Detector

2.0 to 18.0 GHz

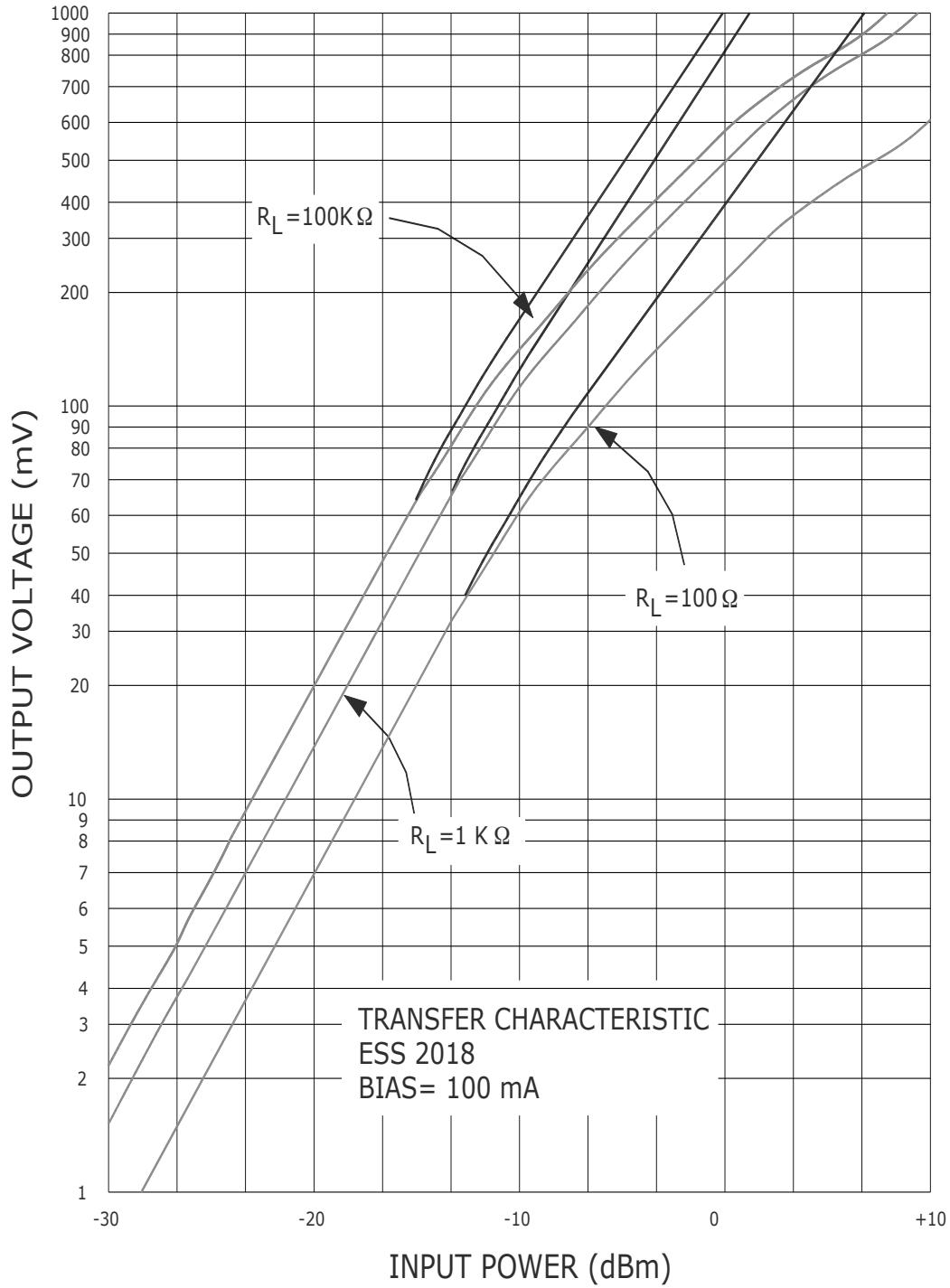
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